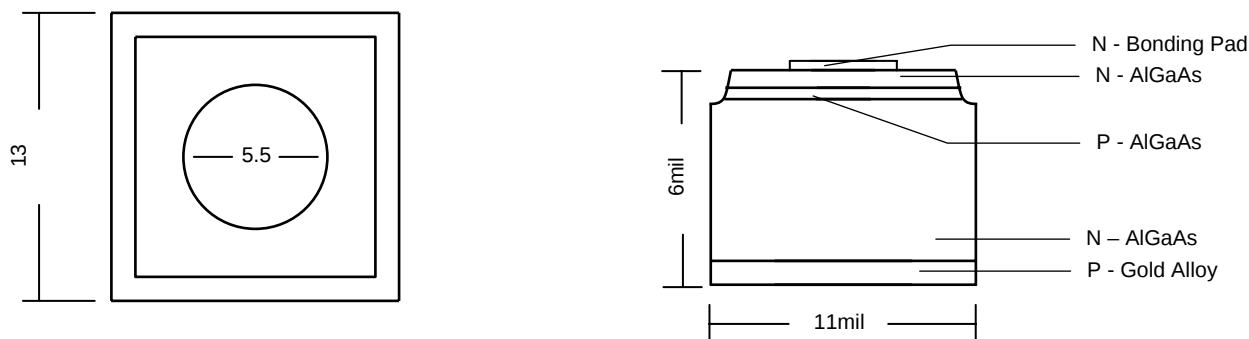


TCM900-10

❖ Outline Dimensions:



❖ Physical Structure:

Chip dimensions		Chip size	13 mil x 13 mil	320 μ m x 320 μ m
		Thickness	6 mil	150 μ m
		Bonding pad	5.5 mil	140 μ m
Electrode	Top	N (cathode)	Gold alloy	
	Backside	P (anode)	Gold alloy	

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	1.40	1.60	V
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Peak Wavelength	λ_P	$I_F = 20\text{mA}$	890	900	910	nm
Spectral Bandwidth	$\Delta\lambda$	$I_F = 20\text{mA}$	-	25	-	nm
Radiant Flux	P_O	$I_F = 20\text{mA}$	0.8	1.2	-	mW
2 nd Peak Emission Ratio	R (λ_2/λ_P)	$I_F = 20\text{mA}$	-	0	0.1	%